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#8 IDS

PATENT & TRADEMARK OFFICE	ATTY. DOCKET NO.	APPLICATION NO.:
	4717-4600	10/069,058
	APPLICANT:	
	Thierry Barge et al.	

FILING DATE:  
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GROUP:

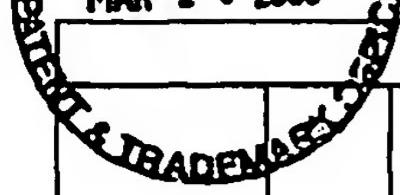
## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MJ	AA	5,589,422	12/1996	Bhat	437	228	
MJ	AB	5,374,564	12/1994	Bruel	437	24	
MJ	AC	6,020,252	2/2000	Aspar et al.	438	458	
MJ	AD	6,403,450 B1	6/2002	Maleville et al.	438	471	
MJ	AE	6,429,104	8/2002	Auberton-Herve	438	527	

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
MJ	AF	EP 0 553 852 A	08/1993	Europe			X	
MJ	AG	EP 0 917 193 A	05/1999	Europe			X	
MJ	AH	EP 0 917 188 A	05/1999	Europe			X	
MJ	AI	FR 2 681 472 A	03/1993	France - (US equivalent 5,374,564)			X	
MJ	AJ	FR 2 777 115 A	10/1999	France - (US equivalent 6,403,450)			X	
MJ	AK	FR 2 774 510 A	08/1999	France - (US equivalent 6,429,104)			X	
MJ	AL	FR 2 761 526 A (US equivalent in English)	10/1998	France - (DE19753494 Abstract in English)			X	
MJ	AM	FR 2 762 136 (with English Abstract)	10/1998	France - (DE19753494 Abstract in English)			X	
MJ	AN	FR 2 761 526 (with English Abstract)	10/1998	France			X	
MJ	AO	FR 2 748 851 A	11/1997	France - (US equivalent 6,020,252)			X	
MJ	AO	DE 197 53494 English Abstract	10/1998	Germany			X	
MJ	AP	JP 10242154 (with English Abstract)	09/1998	Japan			X	

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## FOREIGN PATENT DOCUMENTS (cont...)

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
<i>MDJ</i>	AQ	JP 5217821 English Abstract	08/1993	Japan			X	
	AR							

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>MDJ</i>	AS	Moriceau, H., et al., "Hydrogen Annealing Treatment Used to Obtain High Quality SOI Surfaces," <u>Annual IEEE International Silicon-on-insulator Conference</u> , Vol. Conf. 24, pp. 37-38, New York (1998).
<i>MDJ</i>	AT	Maszara, W.P., et al., "Quality of SOI Film After Surface Smoothing With Hydrogen Annealing, Touch Polishing," <u>Proceedings of the 1997 IEEE International SOI Conference</u> , pp. 130-131, New York (1997).
<i>MDJ</i>	AU	Sato, N., et al., "Hydrogen Annealed Silicon-on-insulator," <u>Applied Physics Letters</u> , Vol. 65, No. 15, pp. 1924-1926, New York (1994).

## EXAMINER

## DATE CONSIDERED

3/29/2004

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.